Abstracts

On-Wafer Characterization, Modelling, and Optimization of InP-Based HEMTs, pin-Photodiodes and Monolithic Receiver-OEICs for Fiber-Optic Communication

D. Kaiser, H. Grosskopf, I. Gyuro, U. Koerner, W. Kuebart, J.-H. Reemtsma and H. Eisele. "On-Wafer Characterization, Modelling, and Optimization of InP-Based HEMTs, pin-Photodiodes and Monolithic Receiver-OEICs for Fiber-Optic Communication." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 567-570.

We will demonstrate results achieved with receiver OEICs consisting of lnGaAs pin-photodiodes and lnAIAs/lnGaAs HEMTs fabricated by low pressure MOVPE. A 3 dB-bandwidth of 1.6 GHz and an open eye at 3.0 Gb/s NRZ modulation of the monolithically integrated photoreceiver were obtained by on-wafer characterization.

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